

# Row-by-Row Coding for Mitigation of Bitline Inter-cell Interference in MLC Flash Memories

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and Storage Technologies

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- P. H. Siegel was supported in part at the Technion by a fellowship from the Lady Davis Foundation and by a Viterbi Leaders Fellowship.

# Outline

- Flash Memory Basics
- Inter-cell Interference (ICI)
- ICI-Mitigating Constrained Codes
- Concluding Remarks

## References - Flash Memory Error Characterization

- [1] Y. Cassuto, M. Schwartz, V. Bohossian, and J. Bruck, "Codes for asymmetric limited-magnitude errors with application to multilevel flash memories," *IEEE Trans. Inf. Theory*, vol. 56, no. 4, pp. 1582-1595, April 2010.
- [2] E. Yaakobi, J. Ma, L. Grupp, P. H. Siegel, S. Swanson, and J. K. Wolf, "Error characterization and coding schemes for flash memories," in *Proc. IEEE Globecom Workshops*, Dec. 2010, pp. 1856-1860.
- [3] Y. Cai, E.F. Haratsch, O. Mutlu, and K. Mai, "Error patterns in MLC NAND flash memory: Measurement, characterization, and analysis," in *Proc. DATE*, March 2012, pp. 521-526.
- [4] J. Moon, J. Lo, S. Lee, S. Kim, S. Choi, and Y. Song, "Statistical characterization of noise and interference in NAND flash memory," in *IEEE Trans. Circuits and Systems - I: Regular Papers*, vol. 60, no. 8, August 2013, pp. 2153-2164.
- [5] Y. Cai, E.F. Haratsch, O. Mutlu, and K. Mai, "Threshold voltage distribution in MLC NAND flash memory: characterization, analysis, and modeling," in *Proc. DATE*, March 2013, pp.1285-1290.
- [6] Y. Cai, O. Mutlu, E.F. Haratsch, and K. Mai, "Program interference in MLC NAND flash memory: Characterization, modeling, and mitigation," in *Proc. IEEE ICCD*, June 2013, pp. 123-130.

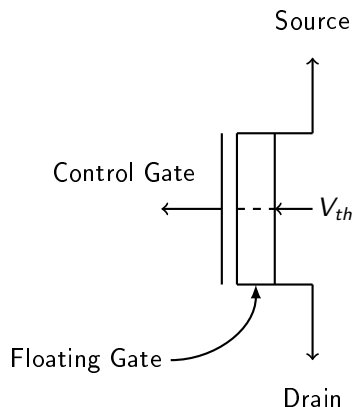
# References - Constrained Codes for Flash Memory

- [1] A. Berman and Y. Birk, "Constrained flash memory programming," *Proc. IEEE Symp. Inf. Theory*, July–August, 2011, pp. 2128–2132.
- [2] R. Motwani, "Hierarchical constrained coding for floating-gate to floating-gate coupling mitigation in flash memory," in *Proc. IEEE Globecom*, December 2011.
- [3] A. Berman and Y. Birk, "Low-complexity two-dimensional data encoding for memory inter-cell interference reduction," *Proc. 27th Conv. IEEE Israel (IEEEI)*, November 2012.
- [4] Y. Kim, B. Kumar, K. L. Cho, H. Son, J. Kim, J. J. Kong, and J. Lee, "Modulation coding for flash memories," in *Proc. ICNC*, Jan. 2013, pp. 961-967.
- [5] M. Qin, E. Yaakobi, and P. H. Siegel, "Constrained codes that mitigate inter-cell interference in read/write cycles for flash memories," *IEEE JSAC*, vol. 32, no. 5, pp. 836-846, May 2014.
- [6] V. Taranalli, H. Uchikawa, and P.H. Siegel, "Error analysis and inter-cell interference mitigation in multi-level cell flash memories," in *Proc. IEEE ICC*, June 2015.

# Flash Memory Basics

# Flash Memory Structure

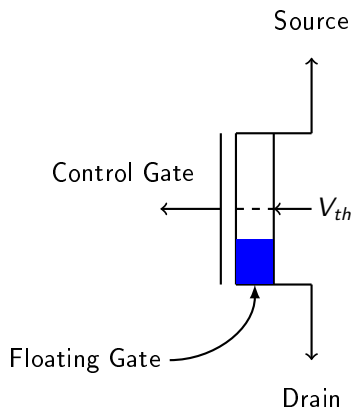
- Floating gate transistor (Cell) – Fundamental data storing unit
- Program a cell to different voltage levels to represent stored bits.



- Incremental Step Pulse Program (ISPP)

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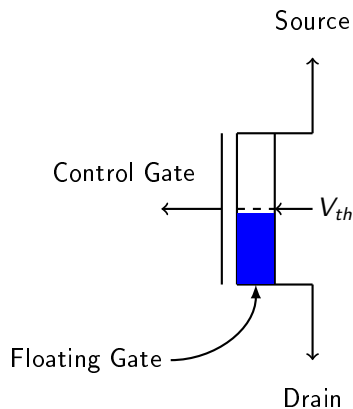


- Incremental Step Pulse Program (ISPP)
- Program, Verify



# Flash Memory Structure

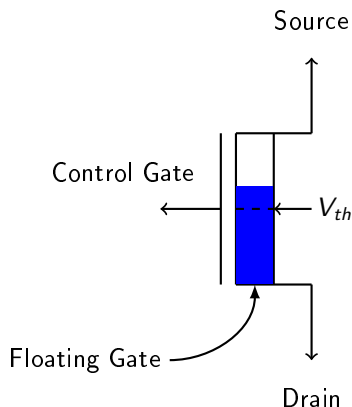
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# Flash Memory Structure

- Common types of NAND Flash
  - Single-Level Cell (SLC) – 1 bit/cell
  - Multi-Level Cell (MLC) – 2 bits/cell
  - Three-Level Cell (TLC) – 3 bits/cell
- Cells → Pages → Smallest unit for program and read operations
- Pages → Blocks → Smallest unit for the erase operation

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# MLC Flash Memory Structure

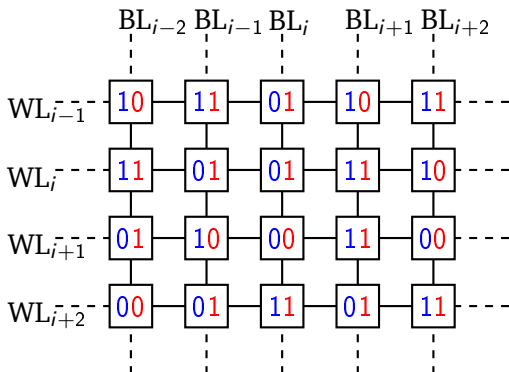
■ Lower Page

■ Upper Page

High Voltage

3	01
2	00
1	10
0	11

Low Voltage

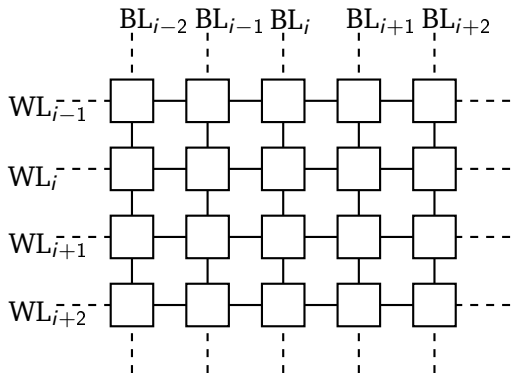


- Typical MLC flash page holds 4K - 16K bytes
- Typical block holds 64 - 128 pages

# Programming MLC Flash Blocks

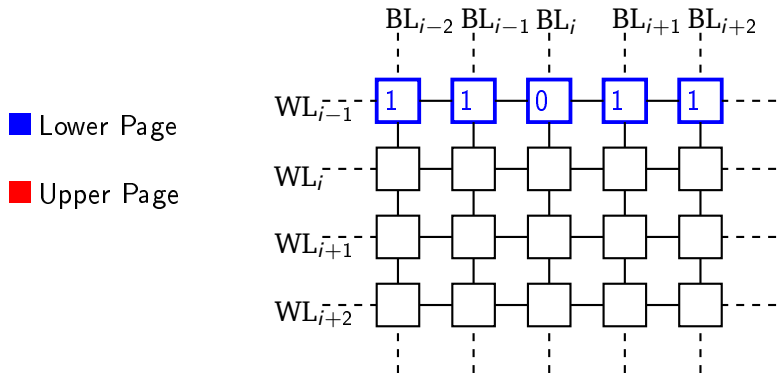
■ Lower Page

■ Upper Page



- Upper and lower pages within wordlines are independent.
- Programming of pages is done row-by-row.

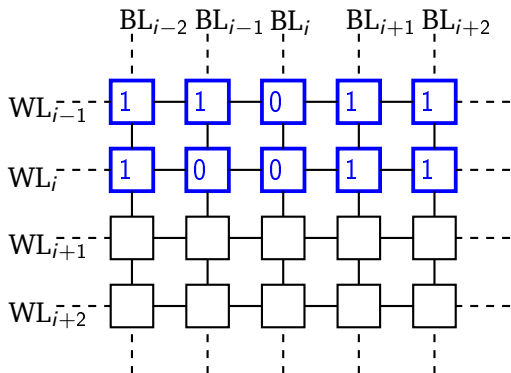
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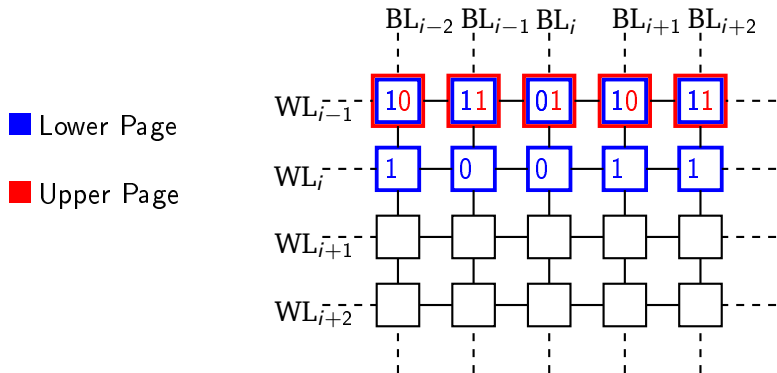
- Lower Page
- Upper Page



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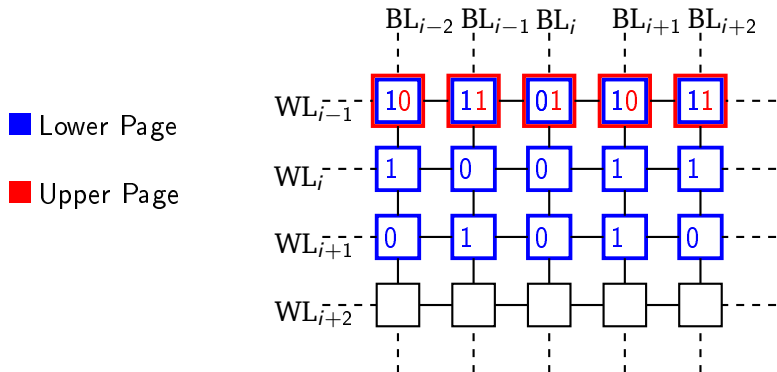


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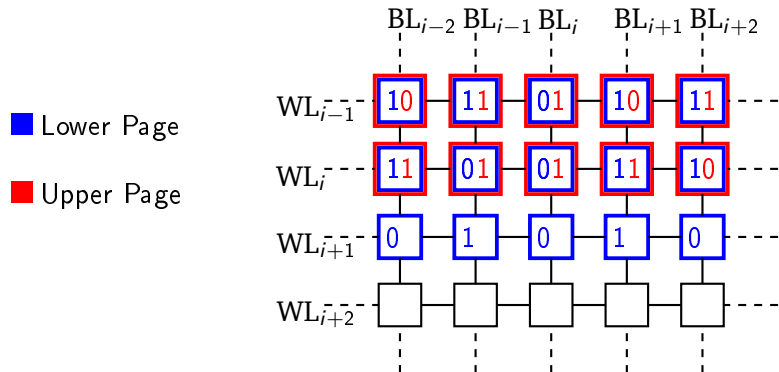
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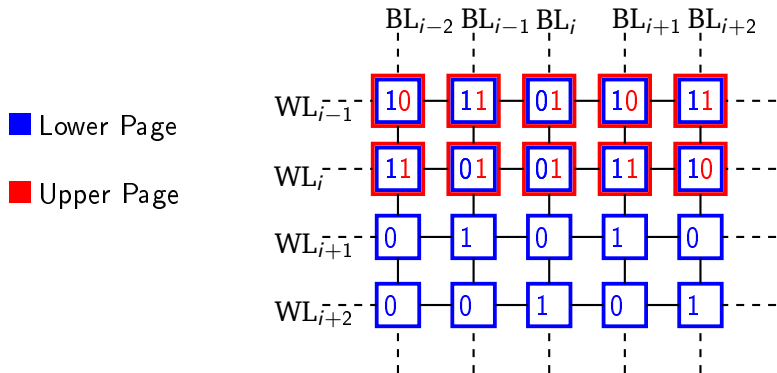
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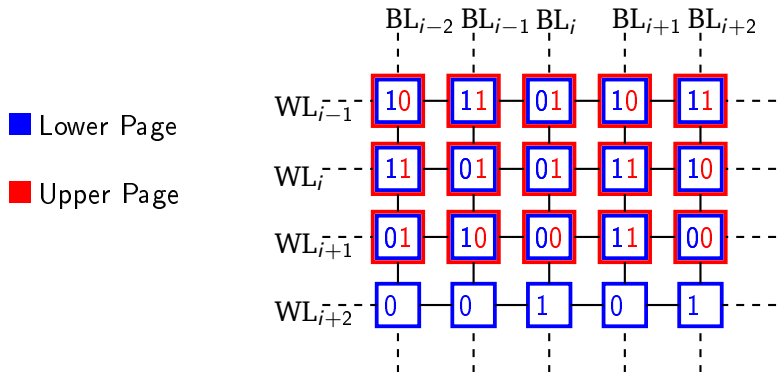
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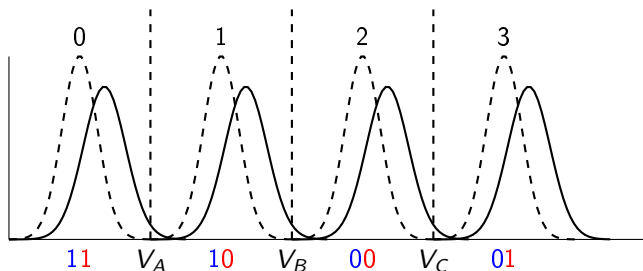
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# Inter-cell Interference (ICI)

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- Parasitic capacitance coupling occurs among neighboring cells.
- This causes random, data dependent errors after cells are programmed.
- ICI-induced errors are a dominant problem for small feature size technology.

## Dominant Cell Errors

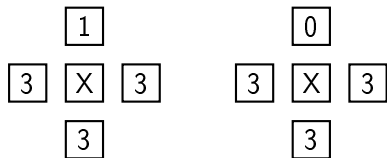
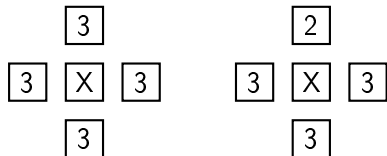


Most cell errors are adjacent cell-level errors in the upward direction:

- 0  $\rightarrow$  1 (upper page error)
- 1  $\rightarrow$  2 (lower page error)
- 2  $\rightarrow$  3 (upper page error)

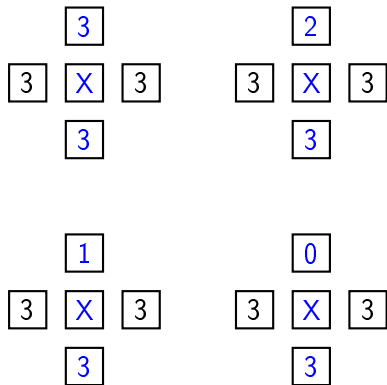


## Dominant Cell Error Patterns



- Neighbor cells programmed to the highest level '3' cause the most ICI.
- Wordline (horizontal) ICI effect is symmetric.
- Bitline (vertical) ICI effect is asymmetric.
- Bitline ICI causes more errors.

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How can we control bitline ICI-induced errors under the constraints of page-oriented, row-by-row programming?

# ICI-Mitigating Constrained Codes

# Dominant Error Patterns - Binary Representations

- Binary representation of dominant cell error patterns:

Cell levels	LU-LU-LU
3-0-3	01-11-01
3-1-3	01-10-01
<u>3-2-3</u>	<u>01-00-01</u>
2-0-3	00-11-01
2-1-3	00-10-01

# Dominant Error Patterns - Binary Representations

- Lower pages of dominant cell error patterns:

Cell levels	LU-LU-LU
3-0-3	01-11-01
3-1-3	01-10-01
<u>3-2-3</u>	<u>01-00-01</u>
2-0-3	00-11-01
2-1-3	00-10-01

# Dominant Error Patterns - Binary Representations

- Upper pages of dominant cell error patterns:

Cell levels	LU-LU-LU
3-0-3	01-11-01
3-1-3	01-10-01
<u>3-2-3</u>	<u>01-00-01</u>
2-0-3	00-11-01
2-1-3	00-10-01

## ICI-Mitigating No-010 Constraint

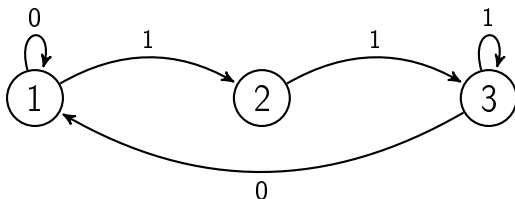
- All patterns except 3-2-3 contain 0-1-0 in lower pages.

Cell levels	LU-LU-LU
3-0-3	01-11-01
3-1-3	01-10-01
<u>3-2-3</u>	<u>01-00-01</u>
2-0-3	00-11-01
2-1-3	00-10-01

- Forbidding 0-1-0 in bitline lower pages eliminates vertical patterns  
3-0-3 3-1-3, 2-0-3, 2-1-3

# ICI-Mitigating Constraints

- The set  $S$  of binary sequences satisfying the no-010 constraint.



- The maximum possible coding efficiency of a code into these sequences is the capacity  $Cap(S)$ :

$$Cap(S) = \lim_{n \rightarrow \infty} \frac{\log_2 |S \cap \{0, 1\}^n|}{n} \approx 0.8114.$$

- This is the highest code rate we could achieve even if we encoded bitline pages directly (i.e., vertically).



# Row-by-Row Coding for Bitline ICI Mitigation

- We present a row-by-row code construction that consists of two steps.
  - Step 1: Probabilistic analysis (for target code rate)
  - Step 2: Code construction using constant-weight codes
- The design method yields codes with the following properties:
  - Encoding is row-by-row and fixed rate.
  - Encoding / decoding a row requires the previous two rows.
  - The code rate can approach the capacity  $Cap(S) \approx 0.8114$  (as the number of wordlines and bitlines approaches infinity).

# Probabilistic Analysis

- We define a stationary Markov process in terms of:
  - Probability mass function  $\pi(x_1x_2)$ ,  $x_1x_2 \in \{0,1\}^2$ ,  
 $0 \leq \pi(x_1x_2) \leq 1$ ,  $\sum_{x_1,x_2 \in \{0,1\}} \pi(x_1x_2) = 1$ .
  - For each  $x_1x_2$ , a conditional probability mass function  
 $P(x_3|x_1x_2)$ ,  $x_3 \in 0,1$ ,  $P(1|x_1x_2) = 1 - P(0|x_1x_2)$ .
- For a binary sequence  $\mathbf{b} = b_1b_2 \dots b_m$ , we define

$$Pr(\mathbf{b}) = \pi(b_1b_2) \prod_{i=3}^m P(b_i|b_{i-2}b_{i-1}).$$

## Probabilistic Analysis (cont.)

- By stationarity, we obtain a system of equations, linear in  $\pi(x_1x_2)$

$$\pi(00)P(0|00) + \pi(10)P(0|10) = \pi(00)$$

$$\pi(00)P(1|00) + \pi(10)P(1|10) = \pi(01)$$

$$\pi(01)P(0|01) + \pi(11)P(0|11) = \pi(10)$$

$$\pi(01)P(1|01) + \pi(11)P(1|11) = \pi(11)$$

- We can express  $\pi(x_1x_2)$  in terms of  $P(0|\tilde{x}_1\tilde{x}_2)$ , and the information rate of the process can be written as

$$R(P) = H(P(x_3|x_1x_2)).$$

## Probabilistic Analysis (cont.)

- To satisfy the no-010 constraint, we set  $P(0|01) = 0$ .
- Then  $P(0|x_1x_2)$ ,  $x_1x_2 \neq 01$  can be chosen to maximize  $R(P)$ , yielding  $R(P) = \text{Cap}(S)$ .
- For our code construction, choose  $n$  and  $P$  such that  $\pi(x_1x_2)n$  and  $P(0|x_1x_2)\pi(x_1x_2)n$  are integers.
- Since  $R(P)$  is continuous in  $P(0|x_1x_2)$ , we can do this for rates arbitrarily close to  $\text{Cap}(S)$ .

# Code Construction

- Define  $p_x = \pi(x0) + \pi(x1)$  and  $p_{x_1x_2} = P(1|x_1x_2)\pi(x_1x_2)$ .
- Let  $\mathbb{C}(m, w)$  be the constant-weight code that consists of all binary sequences of length  $m$  and weight  $w$ .
- The encoding process uses three codes built from various  $\mathbb{C}(m, w)$ :

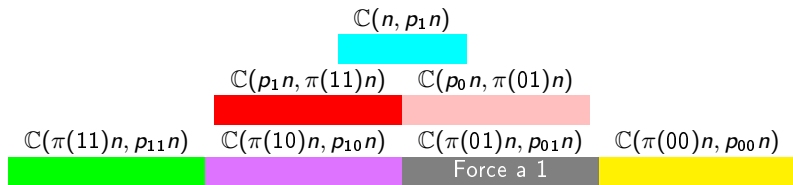
$$\mathbb{C}^1 = \mathbb{C}(n, p_1 n)$$

$$\mathbb{C}^2 = \mathbb{C}(p_0 n, \pi(01)n) \times \mathbb{C}(p_1 n, \pi(11)n)$$

$$\mathbb{C}^3 = \mathbb{C}(\pi(00)n, p_{00}n) \times \mathbb{C}(\pi(01)n, p_{01}n) \times \\ \mathbb{C}(\pi(10)n, p_{10}n) \times \mathbb{C}(\pi(11)n, p_{11}n).$$

- $P(0|01) = 0$  implies  $p_{01} = \pi(01)$ , so  $\mathbb{C}(\pi(01)n, p_{01}n) = \{\underline{1}\}$ .

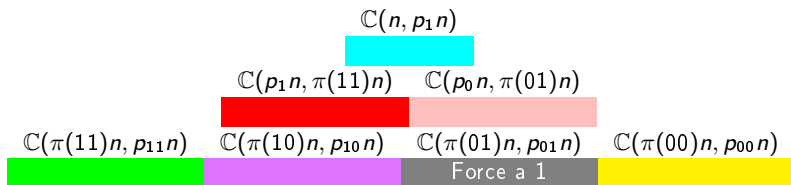
# Encoding



- $WL_1$ : Encode using  $\mathbb{C}(n, p_1 n)$ .
- $WL_2$ : Find index sets  $I_0$  and  $I_1$  where values in  $WL_1$  are 0 and 1. For corresponding index sets in  $WL_2$ , encode using  $\mathbb{C}(p_0 n, \pi(01)n)$  and  $\mathbb{C}(p_1 n, \pi(11)n)$
- $WL_i$ ,  $i \geq 3$ : Find index sets  $I_{x_1 x_2}$  where value in  $WL_{i-2}$ ,  $WL_{i-1}$  is  $x_1 x_2$ . For corresponding sets of indices in  $WL_i$ , encode using the four codes  $\mathbb{C}(\pi(x_1 x_2)n, p_{x_1 x_2} n)$ ,  $x_1 x_2 \in \{0, 1\}^2$ .

Example: Target rate  $R(P) = \frac{4}{5}$

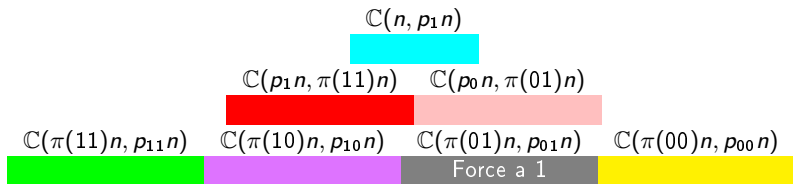
$WL_1$	1	0	1	0	1	1	1	0	0	1
$WL_2$	1	1	0	1	1	0	1	0	0	1
$WL_3$	1	1	1	1	0	0	0	1	0	1



- $p_1 = \frac{3}{5}$  ;  $p_0 = \frac{2}{5}$ .
- $\pi(11) = \frac{2}{5}$  ;  $\pi(x_1 x_2) = \frac{1}{5}$ ,  $x_1 x_2 \neq 11$ .
- $P(1|11) = P(1|10) = P(1|00) = \frac{1}{2}$  so  $\mathbb{C}^2$  and  $\mathbb{C}^3$  use balanced codes.
- Since  $\lim_{n \rightarrow \infty} (1/n) \log_2 |\mathbb{C}(n, \lfloor \beta n \rfloor)| = H(\beta)$ , the asymptotic encoding rate of the balanced codes is 1.
- The asymptotic rate of code  $\mathbb{C}^3$  is therefore  $4/5$ .

# Encoding: $WL_4$

$WL_1$	1	0	1	0	1	1	1	0	0	1
$WL_2$	1	1	0	1	1	0	1	0	0	1
$WL_3$	1	1	1	1	0	0	0	1	0	1
$WL_4$	1	1	1	0	0	1	1	1	0	0



- Rows  $WL_{i-2}, WL_{i-1}$ ,  $i \geq 3$  have a **P-typical** distribution of bitline pairs  $x_1 x_2$ .
- Since the asymptotic rate of  $\mathbb{C}(\pi(ab)n, p_{ab}n)$  is  $H(P(1|ab))$ , and its proportional length is  $\pi(ab)$ , the asymptotic rate of the coding scheme for general distribution  $P$  is  $R(P)$ .
- The overall rate of the ICI-mitigating scheme is  $R = \frac{1}{2}(1 + R(P))$ , or  $R=0.9$  in the example.



# Decoding

$WL_1$	1	0	1	0	1	1	1	0	0	1
$WL_2$	1	1	0	1	1	0	1	0	0	1
$WL_3$	1	1	1	1	0	0	0	1	0	1
$WL_4$	1	1	1	0	0	1	1	1	0	0
$WL_5$	1	0	1	0	0	1	1	0	1	1

- $WL_1$ : Decode using  $\mathbb{C}(n, p_1 n)$ .
- $WL_2$ : Find index sets  $I_x$  where value in  $WL_1$  is  $x$ , for  $x \in \{0, 1\}$ .  
For corresponding index sets in  $WL_2$ , decode using  $\mathbb{C}(p_x n, \pi(x) n)$ .
- $WL_i, i \geq 3$ :  
Find index sets  $I_{x_1 x_2}$  where value in  $WL_{i-2}, WL_{i-1}$  is  $x_1 x_2$ .  
For corresponding sets of indices in  $WL_i$ , decode using  $\mathbb{C}(\pi(x_1 x_2) n, p_{x_1 x_2} n)$

## Concluding Remarks

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- Our code construction assumes the use of efficient encoding and decoding algorithms for constant-weight codes.
- It can be extended to any finite-memory, bitline ICI-mitigating constraint in vertical **lower** pages (resp. **upper**) pages.
- It can also be used independently with a wordline ICI-mitigating constrained code on horizontal **upper** pages (resp. **lower**) pages. The overall rate is then the average of the two code rates.

## Concluding Remarks

- Our construction is an embodiment of the row-by-row coding method proposed in:

Ido Tal, Tuvi Etzion, and Ron M. Roth,  
“On Row-by-Row Coding for 2-D Constraints,”  
*IEEE Transactions on Information Theory*, vol. 55, no. 8,  
August 2009, pp. 3565–3575.

- Extensions to 2-dimensional constrained coding with vertical *data strips* and *merging strips* are described there.

## Extensions

- One can allow the bitline ICI pattern 010 to appear with a specified **nonzero** probability and carry out a similar probabilistic analysis and code construction based upon constant-weight codes.
- One can then combine the row-by-row encoding with a systematic error-correcting code, potentially yielding higher rates and good performance, depending on the probability of a bitline ICI error [Buzaglo, et al., ISIT 2015]. (illustrated for SLC no-101 constraint)

$WL_1$	1	1	0	1	0	0	0	1	$PB_1$
$WL_2$	1	0	1	1	0	1	0	1	$PB_2$
$WL_3$	1	0	0	0	1	1	0	1	$PB_3$
$WL_4$	0	1	0	1	1	1	0	0	$PB_4$

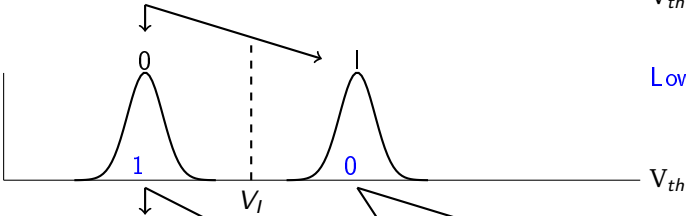
- The analysis of the asymptotic rate and performance of this scheme poses several interesting and challenging problems.

Thank you.

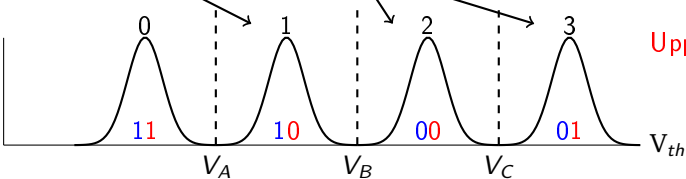
# Programming MLC Flash Cells



Initial State



Lower Page Program



Upper Page Program

# Reading MLC Flash Cells

